

## Supplementary Material

# A win-win combination to inhibit persistent organic pollutant formation via the co-incineration of polyvinyl chloride e-waste and sewage sludge

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The SM contains 4 pages of additional information and includes three tables.

**Table S1.** Instrument conditions for the analysis of PCDD/Fs and dioxin-like PCBs by GC-MSMS.

<b>GC conditions</b>	
Column	Agilent DB-5 MS UI (60 m × 250 μm × 0.25 μm)
Injection volume	1 μL
Injector temperature	300 °C
Injection mode	Splitless
Oven program for PCDD/Fs	Initial: 80 °C (2 minutes) Ramp at 60 °C/min to 140 °C (no hold) Ramp at 20 °C/min to 200 °C (1 minute) Ramp at 3 °C/min to 300 °C (7 minutes)
Oven program for dl-PCBs	Initial: 90 °C (1 minute) Ramp at 20 °C/min to 180 °C (1 minute) Ramp at 3 °C/min to 285 °C (no hold)
He (carrier gas) flow	1 mL/min
<b>MS conditions</b>	
Operation mode	Electron ionization (EI) Multiple Reaction Monitoring (MRM)
Ionization voltage	70 eV
Transfer line temperature	290 °C
Source temperature	280 °C
Quadrupole temperature	150 °C
MS resolution	Unit
He (quench gas) flow	2.25 mL/min
N <sub>2</sub> (collision gas) flow	1.5 mL/min

**Table S2.** MSMS parameters and collision energy for the analysis of native and <sup>13</sup>C-labelled PCDD/Fs.

Time segment	Analyte	Precursor ion (m/z)	Product ion (m/z)	Dwell (ms)	Collision energy (eV)
1 TCDD/F	TCDF	303.9	240.9	100	40
		305.9	242.9	100	40
	<sup>13</sup> C-TCDF	315.9	251.9	20	40
		317.9	253.9	20	40
	TCDD	319.9	256.9	100	26
		321.9	258.9	100	26
	<sup>37</sup> Cl-TCDD	327.9	198	20	40
		327.9	263	20	26
	<sup>13</sup> C-TCDD	331.9	267.9	20	26
333.9		269.9	20	26	
2 PeCDD/F	PeCDF	337.9	274.9	100	40
		339.9	276.9	100	40
	<sup>13</sup> C-PeCDF	349.9	285.9	20	40
		351.9	287.9	20	40
	PCDD	353.9	290.9	100	26
		355.9	292.9	100	26
	<sup>13</sup> C-PeCDD	365.9	301.9	20	26
367.9		303.9	20	26	
3 HxCDD/F	HxCDF	373.8	310.9	100	40
		375.8	312.9	100	40
	<sup>13</sup> C-HxCDF	385.8	321.9	20	40
		387.8	323.9	20	40
	HxCDD	389.8	326.9	100	26
		391.8	328.8	100	25
	<sup>13</sup> C-HxCDD	401.8	337.9	20	26
403.8		339.8	20	26	
4 HpCDD/F	HpCDF	407.8	344.8	100	40
		409.8	346.8	100	40
	<sup>13</sup> C-HpCDF	419.8	355.8	20	40
		421.8	357.8	20	40
	HpCDD	423.8	360.8	100	24
		425.8	362.8	100	24
	<sup>13</sup> C-HpCDD	435.8	371.8	20	26
437.8		373.8	20	24	
5 OCDD/F	OCDF	441.7	378.8	150	40
		443.7	380.8	150	40
	OCDD	457.7	394.8	150	24
		459.7	396.8	150	24
	<sup>13</sup> C-OCDD	469.7	405.8	20	24
		471.7	407.8	20	24

**Table S3.** MSMS parameters and collision energy for the analysis of native and <sup>13</sup>C-labelled dioxin-like PCBs.

Time segment	Analyte	Precursor ion (m/z)	Product ion (m/z)	Dwell (ms)	Collision energy (eV)
1 tetra- and penta-PCBs	tetra-PCB	289.9	219.9	200	25
		291.9	221.9	200	25
	<sup>13</sup> C-tetra-PCB	301.9	232	20	25
		303.9	234	20	25
	<sup>13</sup> C-penta-PCB	335.9	265.9	20	30
		337.9	267.9	20	30
2 penta- and hexa-PCBs	penta-PCB	323.9	253.9	200	30
		325.9	255.9	200	30
	<sup>13</sup> C-penta-PCB	335.9	265.9	20	30
		337.9	267.9	20	30
	<sup>13</sup> C-hexa-PCB	369.9	299.9	20	30
		371.9	301.9	20	30
3 hexa- and hepta-PCBs	hexa-PCB	357.8	287.9	100	30
		359.8	289.9	100	30
	<sup>13</sup> C-hexa-PCB	369.9	299.9	20	30
		371.9	301.9	20	30
	hepta-PCB	393.8	323.9	100	30
		395.8	325.9	100	30
	<sup>13</sup> C-hepta-PCB	405.8	335.8	20	30
		407.8	337.8	20	30

L: labelled